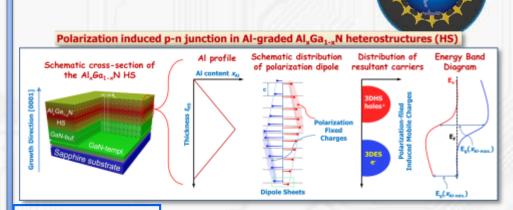


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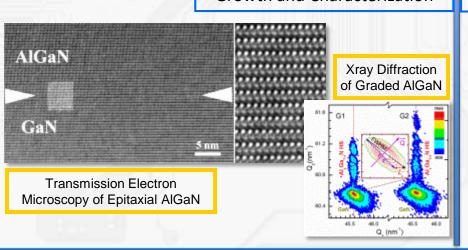


- GaN, AIN, and InN growth and characterization
- Novel wide bandgap device fabrication
- GaN Devices from Fundamental Materials



Novel Devices

Growth and Characterization



GaN Devices from Fundamental Materials

Polarization doped pn-junction shows classical diode I-V response similar to impurity doped pn-junction.

